

# High Voltage Power MOSFET w/ Extended FBSOA

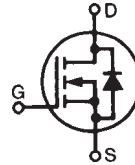
## IXTK5N250 IXTX5N250

$$V_{DSS} = 2500V$$

$$I_{D25} = 5A$$

$$R_{DS(on)} \leq 8.8\Omega$$

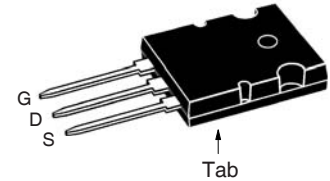
N-Channel Enhancement Mode  
Avalanche Rated  
Guaranteed FBSOA



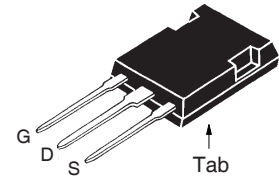
Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	2500	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	2500	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	5	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	20	A
$I_A$	$T_C = 25^\circ C$	2.5	A
$E_{AS}$	$T_C = 25^\circ C$	2.5	J
$P_D$	$T_C = 25^\circ C$	960	W
$T_J$		-55 to +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 to +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
$F_C$	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb.
<b>Weight</b>	TO-264	10	g
	PLUS247	6	g

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	2500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1mA$	2.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = 2kV$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 4 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			8.8 $\Omega$

### TO-264 (IXTK)



### PLUS247 (IXTX)



G = Gate      D = Drain  
S = Source    Tab = Drain

### Features

- Avalanche Rated
- Fast Intrinsic Diode
- Guaranteed FBSOA at  $75^\circ C$
- Low Package Inductance

### Advantages

- Easy to Mount
- Space Savings

### Applications

- High Voltage Power Supplies
- Capacitor Discharge
- Pulse Circuits

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
$g_{fs}$	$V_{DS} = 50\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	3.0	4.5	6.0	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		8560		pF
$C_{oss}$			315		pF
$C_{rss}$			90		pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		33		ns
$t_r$			20		ns
$t_{d(off)}$			90		ns
$t_f$			44		ns
$Q_{g(on)}$		$V_{GS} = 10\text{V}$ , $V_{DS} = 1000\text{V}$ , $I_D = 0.5 \cdot I_{D25}$		200	
$Q_{gs}$			28		nC
$Q_{gd}$			70		nC
$R_{thJC}$				0.13	$^\circ\text{C/W}$
$R_{thCS}$			0.15		$^\circ\text{C/W}$

### Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 2000\text{V}$ , $I_D = 0.11\text{A}$ , $T_C = 75^\circ\text{C}$ , $tp = 3\text{s}$	220		W

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
$I_S$	$V_{GS} = 0\text{V}$			5	A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			20	A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5	V
$t_{rr}$	$I_F = 2.5\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 100\text{V}$		1.2		$\mu\text{s}$

Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

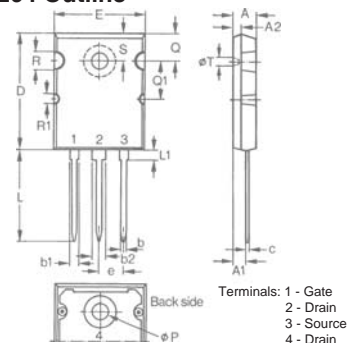
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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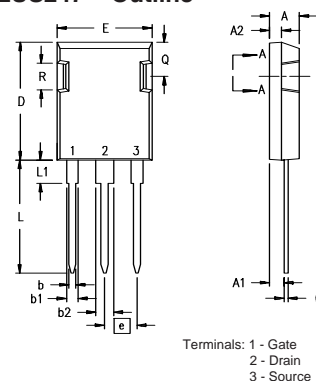
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

### TO-264 Outline



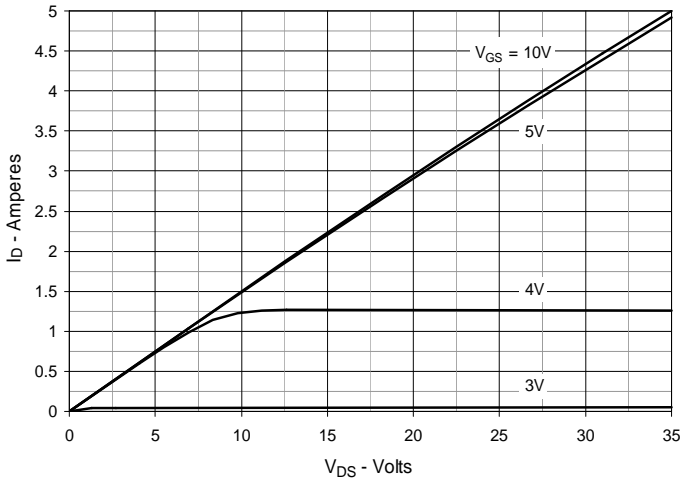
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

### PLUS247™ Outline

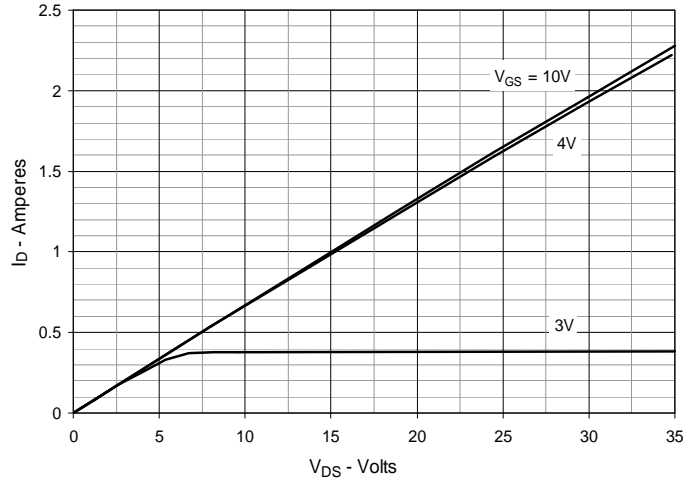


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
b2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

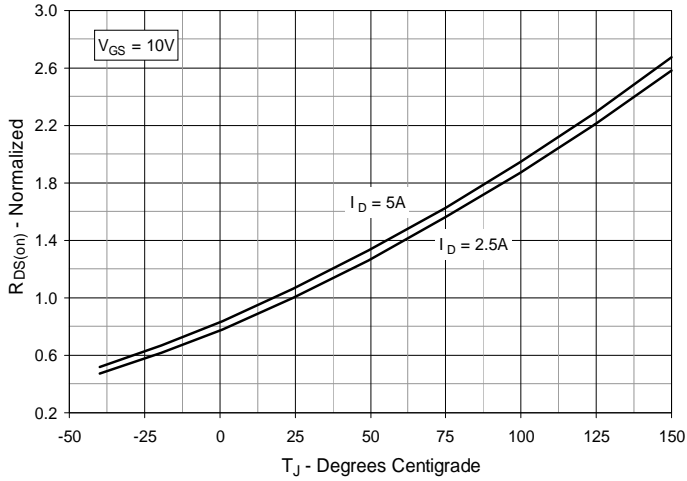
**Fig. 1. Output Characteristics @ T<sub>J</sub> = 25°C**



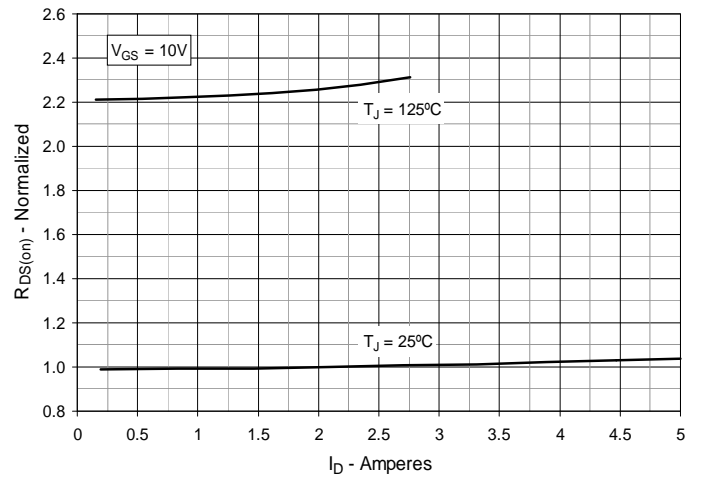
**Fig. 2. Output Characteristics @ T<sub>J</sub> = 125°C**



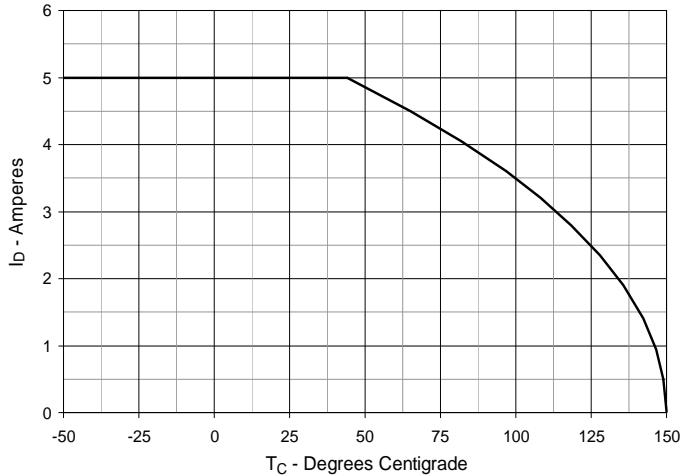
**Fig. 3. R<sub>DS(on)</sub> Normalized to I<sub>D</sub> = 2.5A Value vs. Junction Temperature**



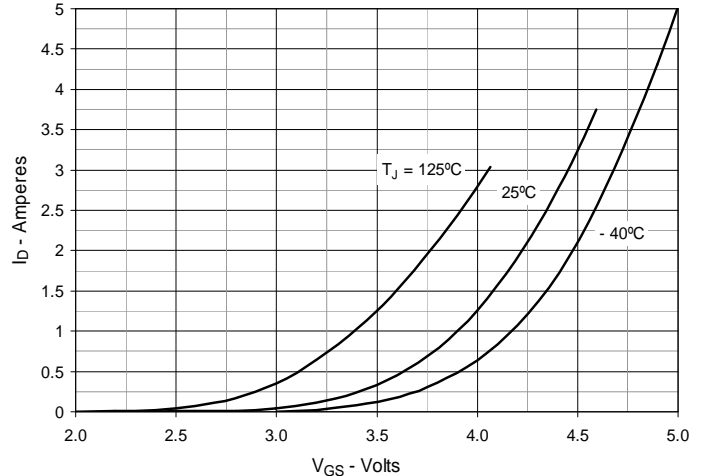
**Fig. 4. R<sub>DS(on)</sub> Normalized to I<sub>D</sub> = 2.5A Value vs. Drain Current**



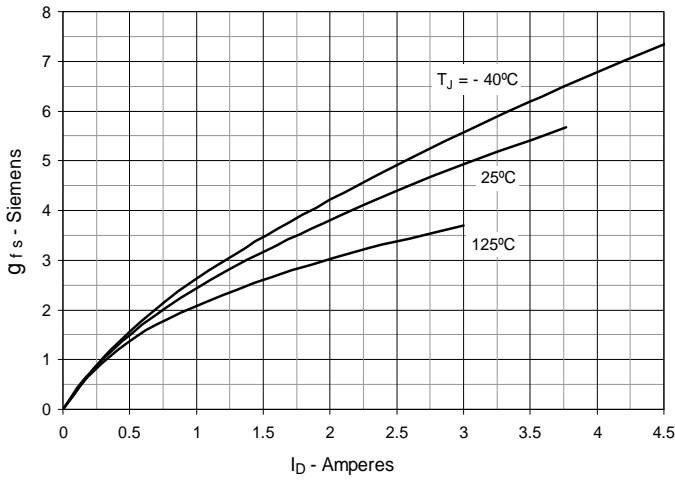
**Fig. 5. Maximum Drain Current vs. Case Temperature**



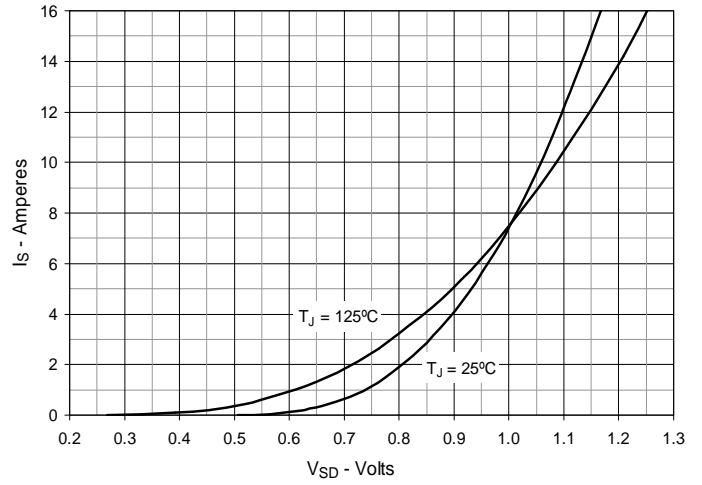
**Fig. 6. Input Admittance**



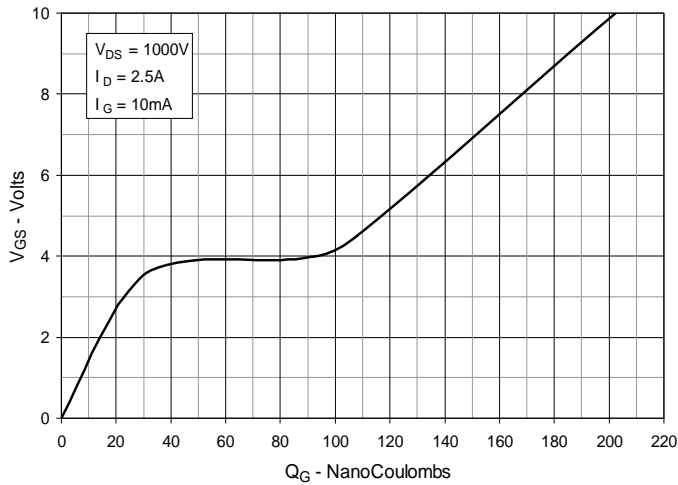
**Fig. 7. Transconductance**



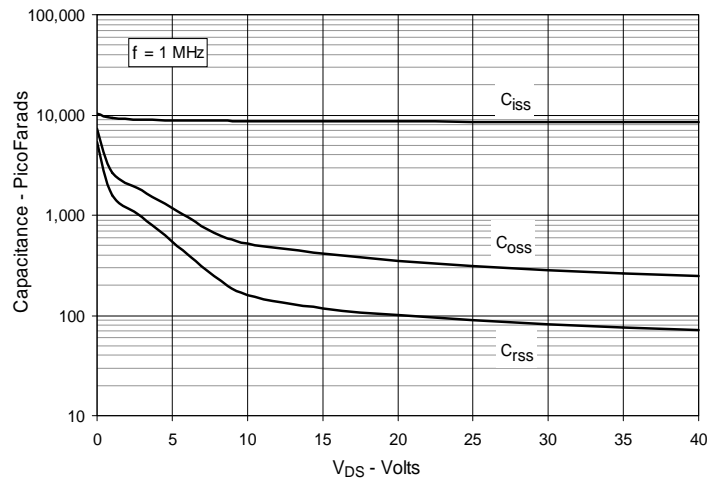
**Fig. 8. Forward Voltage Drop of Intrinsic Diode**



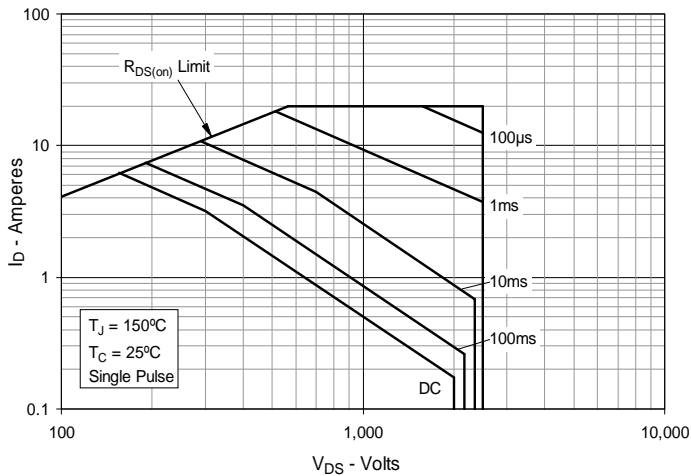
**Fig. 9. Gate Charge**



**Fig. 10. Capacitance**



**Fig. 11. Forward-Bias Safe Operating Area  
@  $T_C = 25^\circ\text{C}$**



**Fig. 12. Forward-Bias Safe Operating Area  
@  $T_C = 75^\circ\text{C}$**

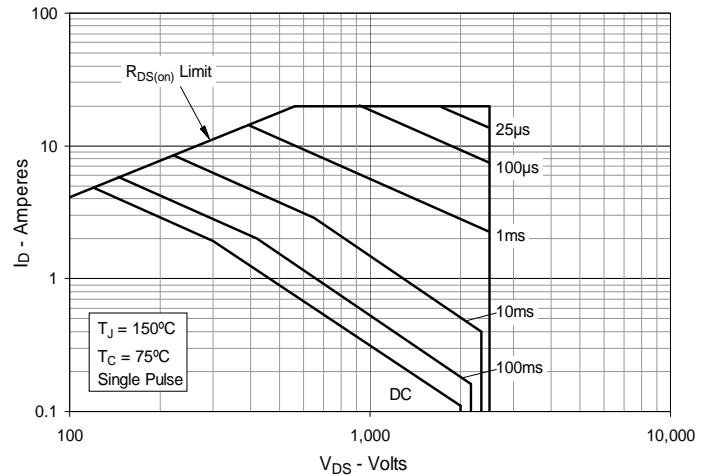


Fig. 13. Maximum Transient Thermal Impedance

